

Features

- 50 mm² Quadrant PIN detector
- High sensitivity
- Low dark current

Description

Low dark current quadrant PIN photodiode with 4 x 12 mm² active area. Metal can type hermetic TO8S package with clear glass window.

Application

- Laser beam position sensor
- Autocollimators
- Optical tweezers
- Ellipsometers

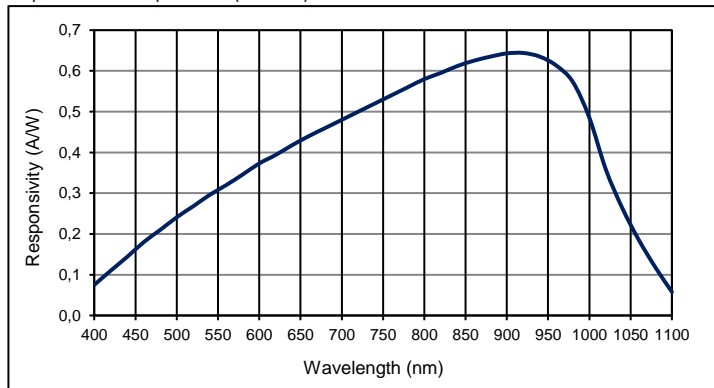
RoHS

2011/65/EU

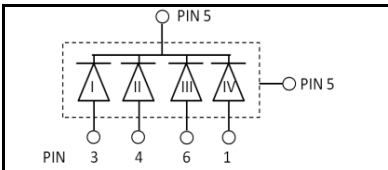
Absolute maximum ratings

Symbol	Parameter	Min	Max	Unit
T _{STG}	Storage temp	-55	125	°C
T _{OP}	Operating temp	-40	100	°C
V _{max}	Max reverse voltage		20	V
I _{PEAK}	Peak DC current		10	mA

Spectral response (23 °C)



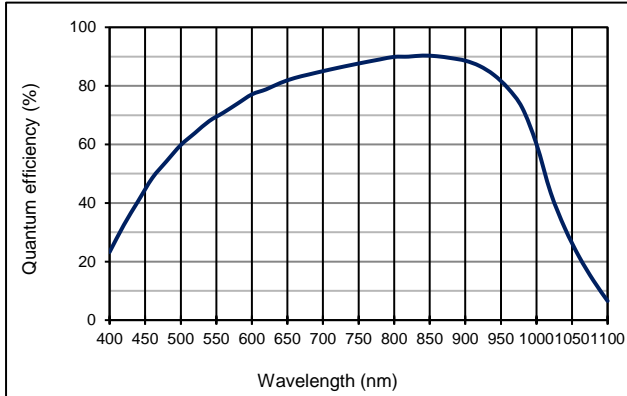
Schematic



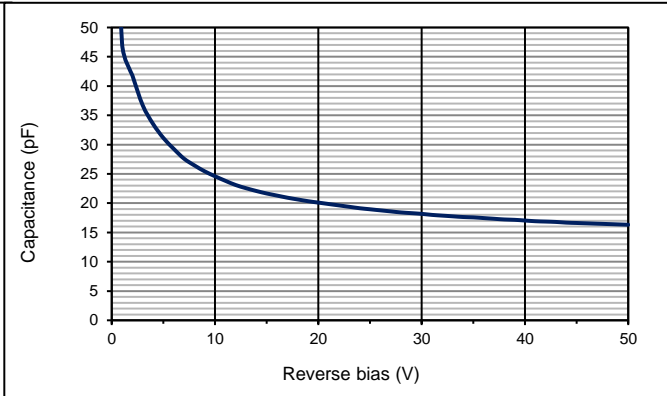
Electro-optical characteristics @ 23 °C

Symbol	Characteristic	Test Condition	Min	Typ	Max	Unit
	Number of elements		4 quadrants			
	Active area		diameter 7980 (total)			μm
	Active area	per element	12			mm ²
	Gap	between elements	42			μm
I _D	Dark current	V _R = 10 V; per element		2.0	5.0	nA
C	Capacitance	V _R = 0 V; per element		120		pF
		V _R = 10 V; per element		20		pF
	Responsivity	λ = 632 nm		0.4		A/W
		λ = 900 nm		0.64		A/W
t _R	Rise time	V _R = 0 V; λ = 850 nm; R _L = 50 Ω		2000		ns
		V _R = 10 V; λ = 850 nm; R _L = 50 Ω		40		ns
	Shunt Resistance	V _R = 5 mV; per element		50		MΩ
	N.E.P.	V _R = 5 V; λ = 900 nm; per element		4 E-14		W/√Hz
V _{BR}	Breakdown voltage	I _R = 2 μA	20	50		V

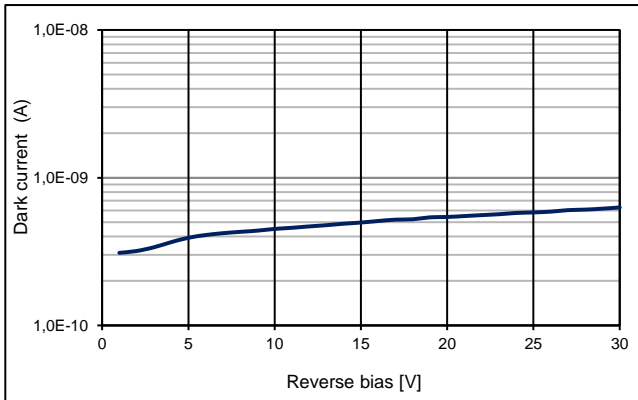
Quantum efficiency (23 °C)



Capacitance as fct of reverse bias (23 °C; per element)



Dark current as fct of bias (23 °C; per element)



Package dimension:

Small quantities: Foam pad, boxed (12 cm x 16.5 cm)

Handling precautions:

- Soldering temperature max. 260 °C for 10 s. The device must be protected against solder flux vapour.
- Minimum pin length is 2 mm.
- For ESD protection standard precautionary measures are sufficient.
- For further questions please refer to document "Instructions for handling and processing".

Disclaimer: Due to our strive for continuous improvement, specifications are subject to change within our PCN policy according to JESD46C.